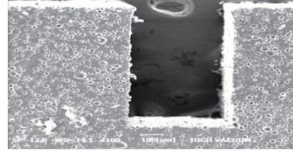
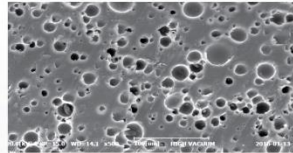


FP1117 FNS Pad (New Pad)



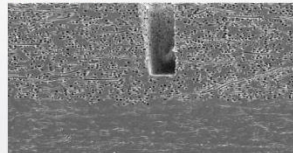
Points of Control

- **Polymer Chemistry**
 - Hardness
 - Abrasion Resistance
- **Pore Size Control**
 - PoreType
 - Pore Density
 - Pore Size
 - Pore Pattern
- **Boundary Location**
 - Porous : Solid Ratio
- **Porosity Control**
 - Fiber : Polymer Ratio



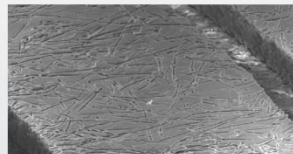
Our New Pad is developed for Chemical Mechanical Planarization process of semiconductor. Innumerable pore exist inside of pad and because of the laminated structure of the pad, it gives outstanding uniformity of target object.
New Pad is optimized in Oxide ILD, STI and W process of semiconductor.

MC8836 INNO Pad (MC 8836)



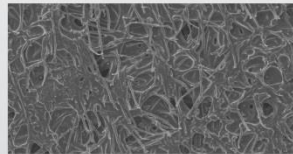
Points of Control

- **Polymer Chemistry**
 - Hardness
 - Abrasion Resistance
- **Fiber Sizes and Orientation**
 - Fiber Type
 - Fiber Density
 - Fiber Size
 - Fiber Pattern
- **Boundary Location**
 - Porous : Solid Ratio
- **Porosity Control**
 - Fiber : Polymer Ratio



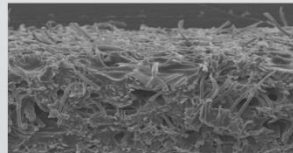
MC-8836 is developed for Chemical Mechanical Planarization process of semiconductor. Innumerable Micro-Channel exist inside of pad and it has superior Removal Rate ability because of these Micro-Channel. Also, because of laminated structure of pad, it gives outstanding uniformity of target object.
MC 8836 is optimized in Wafer Polishing process.

CW PAD Pad (CW Pad)



Product features

- Polyester Nonwoven Fabric
- No Diamond Disk. Nylon brush is used for remove Debris.
- Used in Tungsten Interconnect Polishing process.
- Pad Size Control is possible.



CW Pad is developed for fine polishing process. It is optimized in Tungsten process and it shows good ability in scratch.
We had been deliver it to IBM and Infineon.